

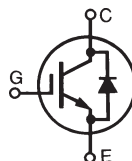
High Voltage, BiMOSFET™ Monolithic Bipolar MOS Transistor

IXBF42N300

$$V_{CES} = 3000V$$

$$I_{C110} = 24A$$

$$V_{CE(sat)} \leq 3.0V$$

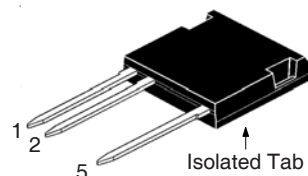


(Electrically Isolated Tab)

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ C$ to $150^\circ C$	3000	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 25	V
V_{GEM}	Transient	± 35	V
I_{C25}	$T_C = 25^\circ C$	60	A
I_{C110}	$T_C = 110^\circ C$	24	A
I_{CM}	$T_C = 25^\circ C$, 1ms	380	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 20\Omega$ Clamped Inductive Load	$I_{CM} = 84$ $V_{CE} \leq 0.8 \cdot V_{CES}$	A
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 82\Omega$, $V_{CE} = 1500V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	240	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ C$
F_C	Mounting Force	20..120 / 4.5..27	Nm/lb.in.
V_{ISOL}	50/60Hz, 1 Minute	3000	V~
Weight		5	g

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ Note 2, $T_J = 125^\circ C$		250	50 μA μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 200 nA
$V_{CE(sat)}$	$I_C = 42A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.5 3.1	3.0 V V

ISOPLUS i4-Pak™



1 = Gate
2 = Emitter

5 = Collector

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 3000V~ Electrical Isolation
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage
- FBSOA Rated
- SCSOA Rated

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Laser Generators
- Capacitor Discharge Circuits
- AC Switches
- Protection Circuits

Symbol Test Conditions

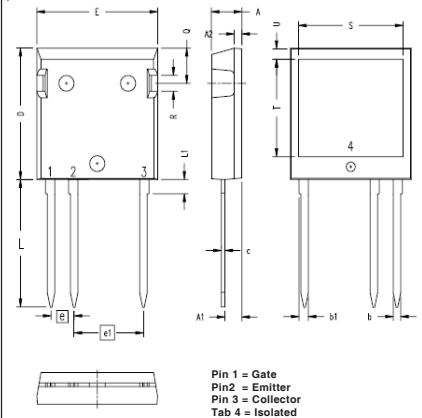
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 42\text{A}, V_{CE} = 10\text{V}$, Note 1	28	45	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		4780	pF
C_{oes}			170	pF
C_{res}			56	pF
R_{Gi}	Gate Input Resistance		3.0	Ω
Q_g	$I_C = 42\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		200	nC
Q_{ge}			28	nC
Q_{gc}			75	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 42, V_{GE} = 15\text{V}$ $V_{CE} = 1500\text{V}, R_G = 20\Omega$		72	ns
t_r			330	ns
$t_{d(off)}$			445	ns
t_f			610	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 42, V_{GE} = 15\text{V}$ $V_{CE} = 1500\text{V}, R_G = 20\Omega$		72	ns
t_r			580	ns
$t_{d(off)}$			460	ns
t_f			490	ns
R_{thJC}				0.52 $^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

ISOPLUS i4-Pak™ (HV) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
e1	.450 BSC		11.43 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max

V_F	$I_F = 42\text{A}, V_{GE} = 0\text{V}$, Note 1		2.5	V
t_{rr}	$I_F = 21\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GE} = 0\text{V}$		1.7	μs
I_{RM}			43	A

Notes:

1. Pulse test, $t < 300\mu\text{s}$, duty cycle, $d < 2\%$.
2. Device must be heatsunk for high-temperature leakage current measurements to avoid thermal runaway.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

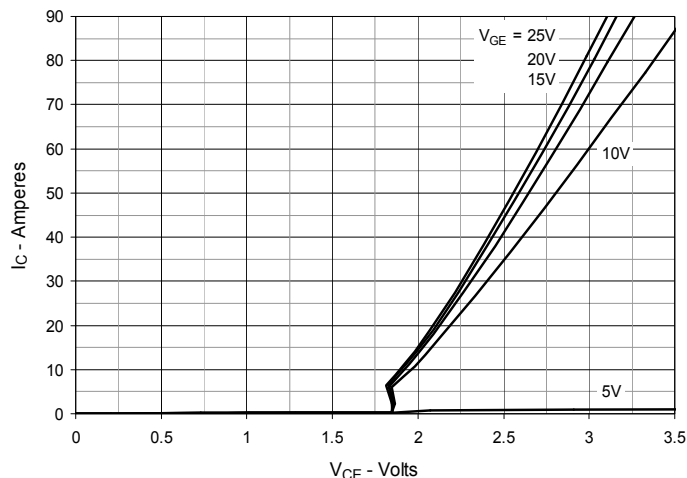
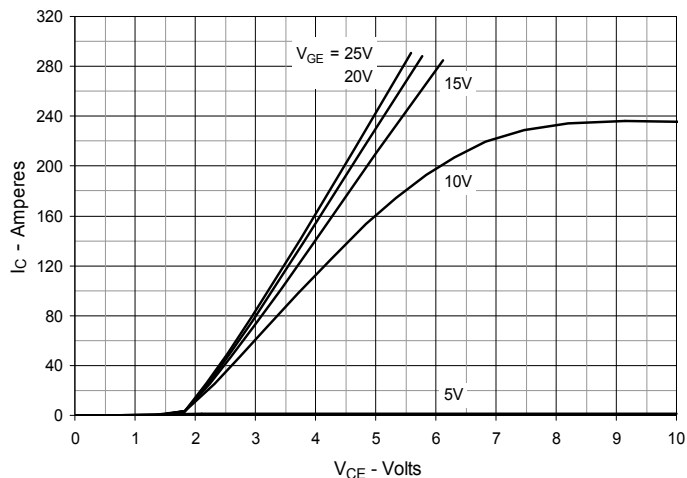
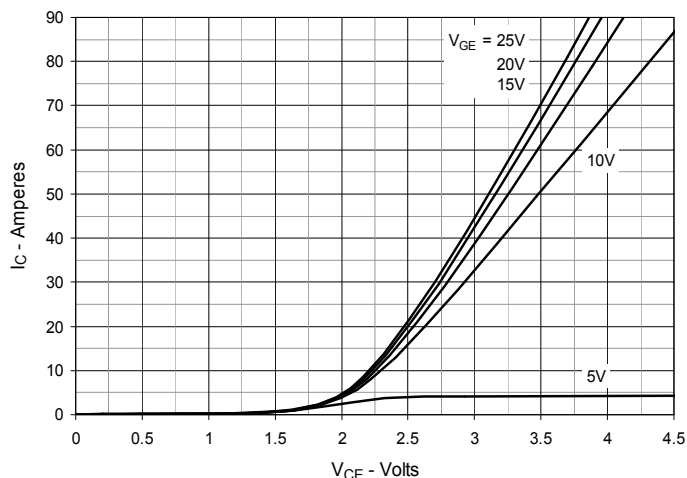
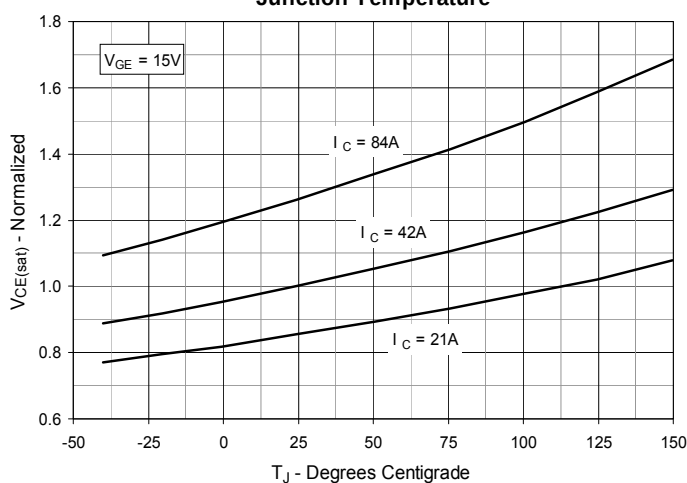
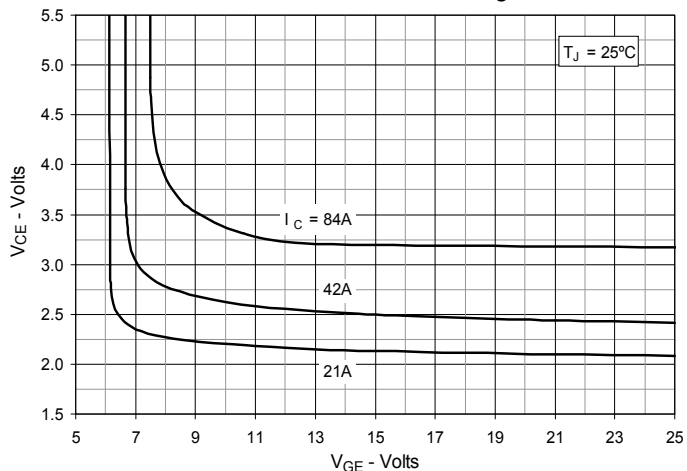
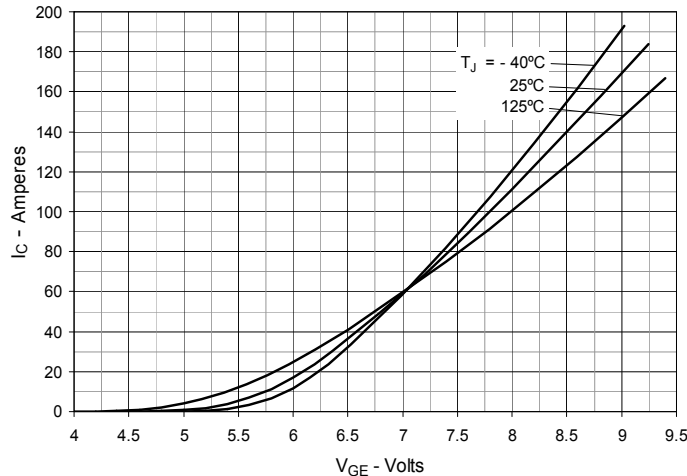
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

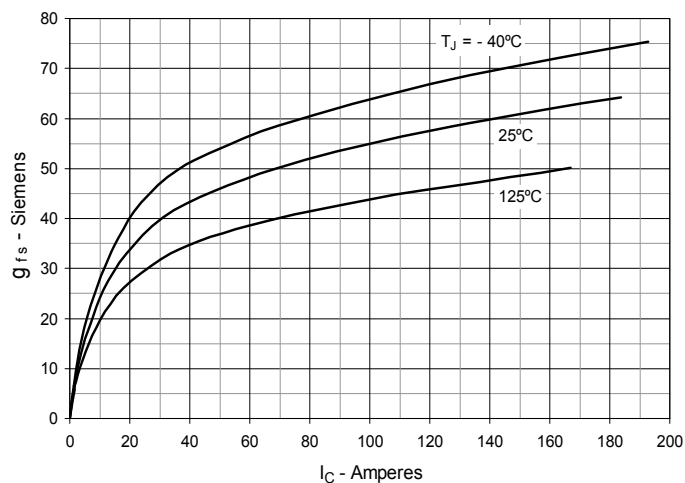


Fig. 8. Forward Voltage Drop of Intrinsic Diode

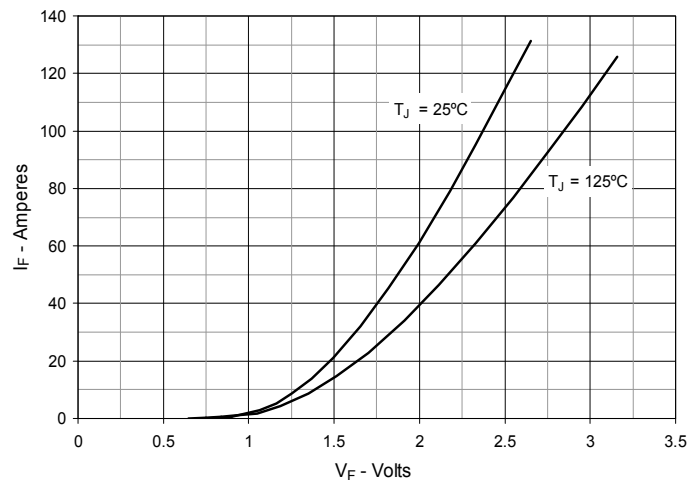


Fig. 9. Gate Charge

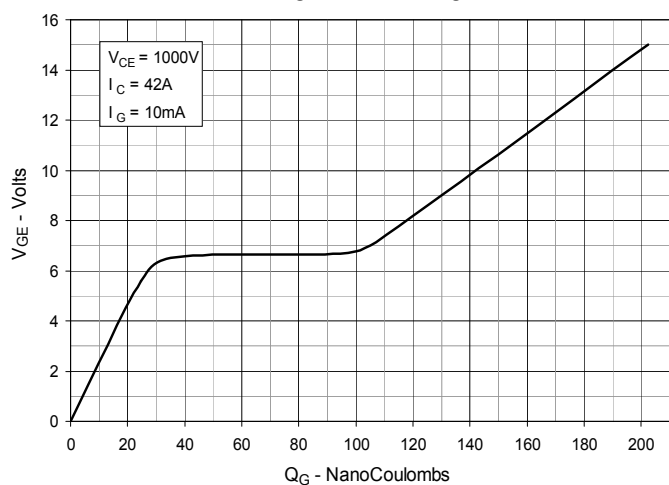


Fig. 10. Capacitance

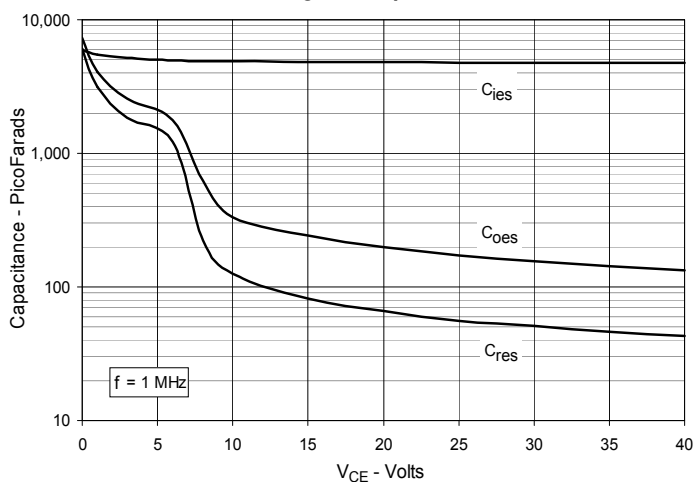


Fig. 11. Reverse-Bias Safe Operating Area

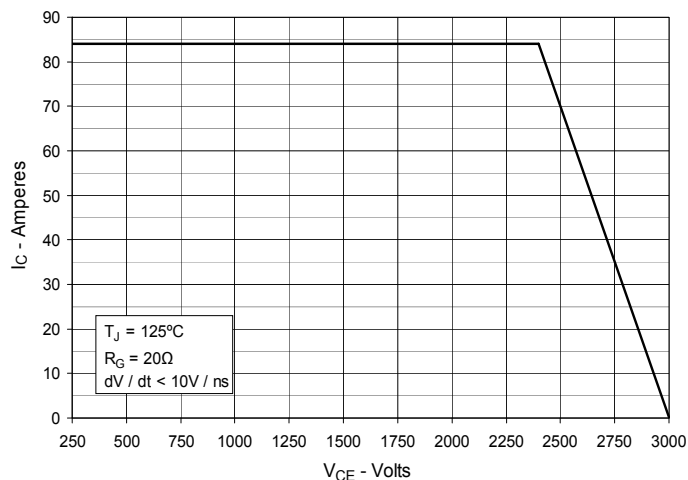


Fig. 12. Maximum Transient Thermal Impedance

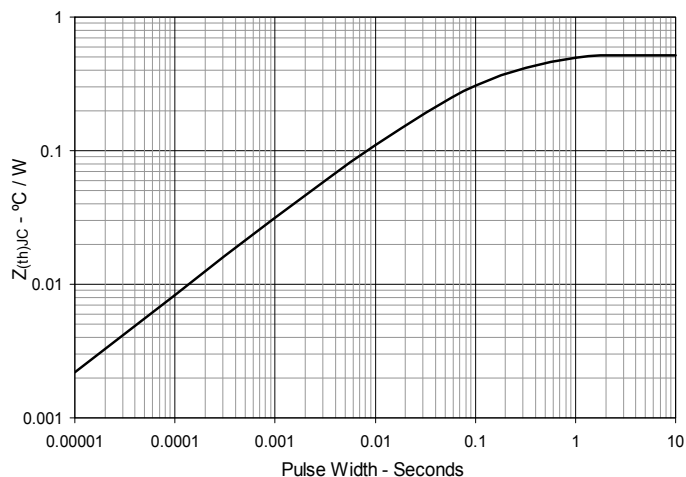


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

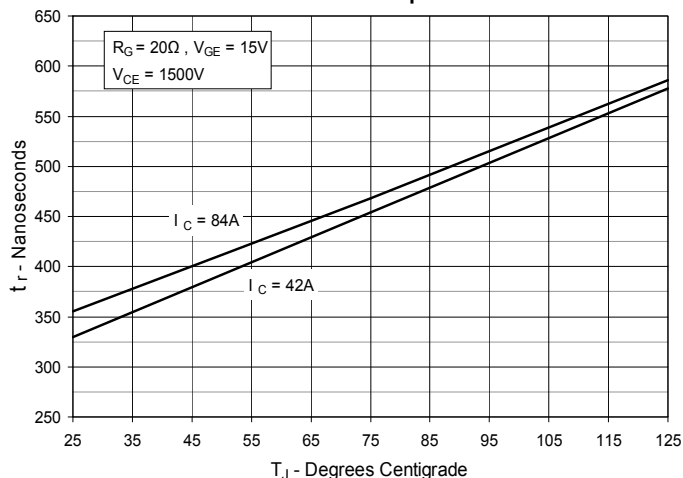


Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

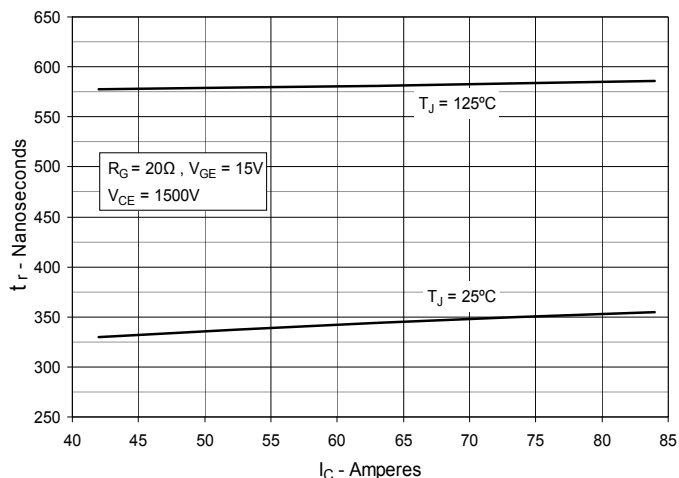


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

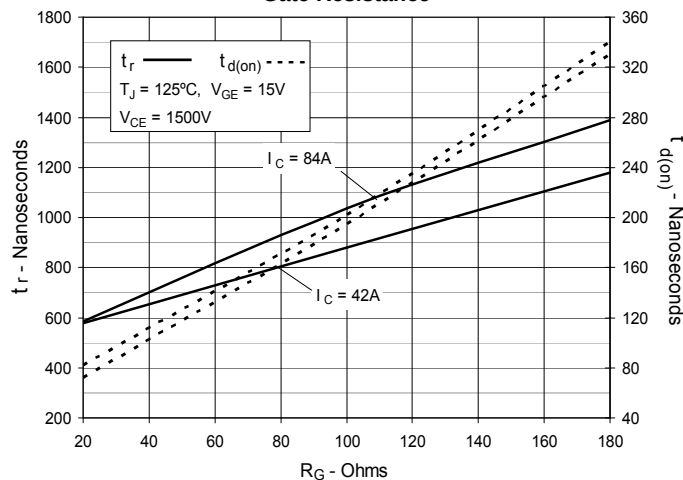


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

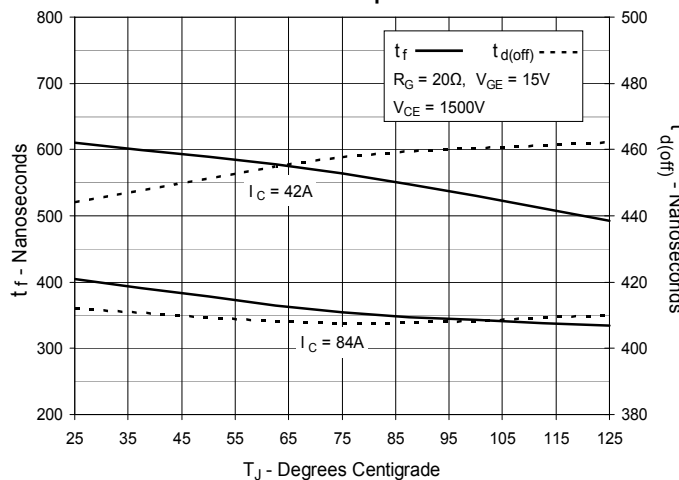


Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

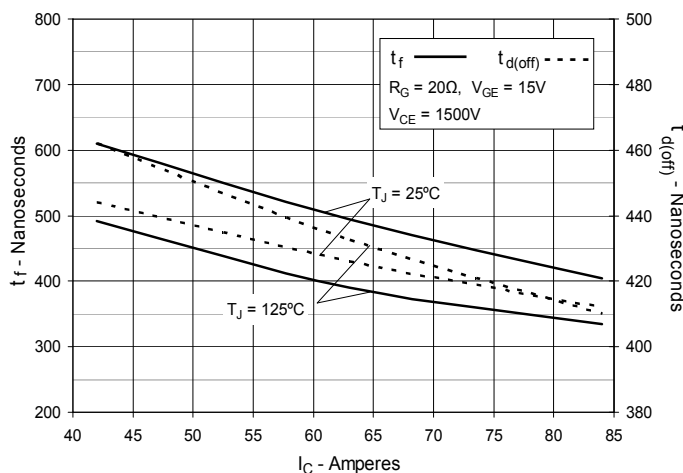


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

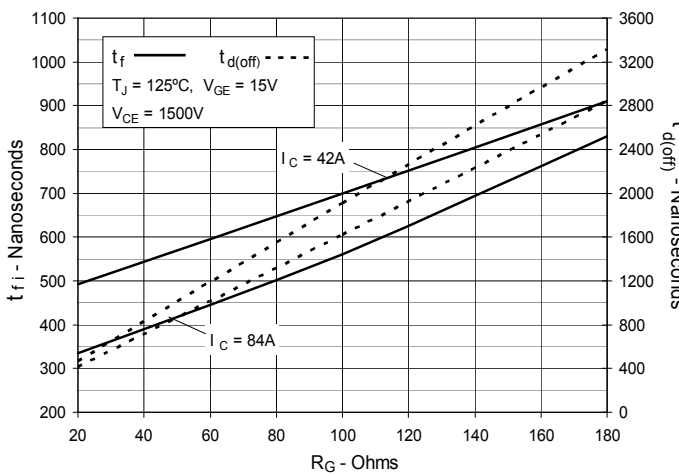
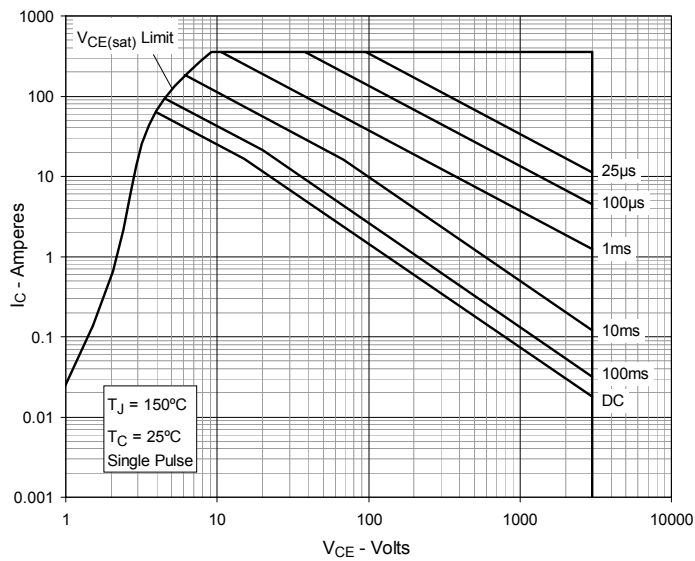
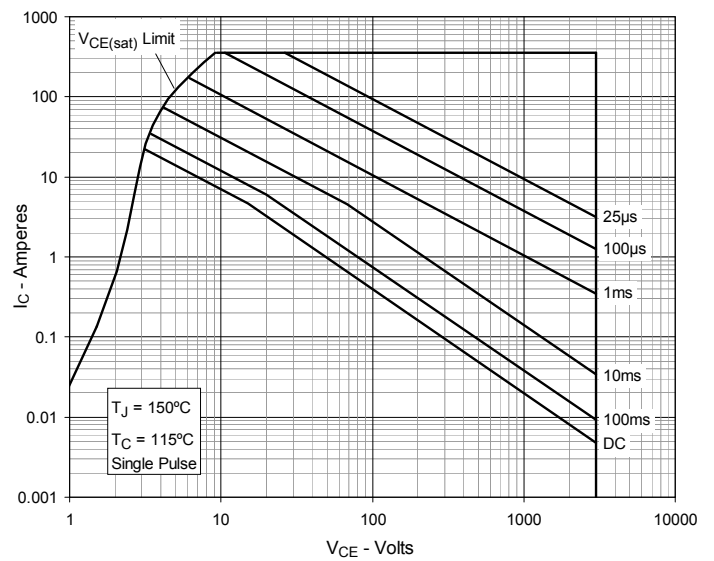


Fig. 19. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

Fig. 20. Forward-Bias Safe Operating Area @ $T_C = 115^\circ\text{C}$




Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.